

### Features

- Uses MHCHXM advanced PerfectMOS technology
- Extremely low on-resistance  $R_{DS(on)}$
- Excellent  $Q_g \times R_{DS(on)}$  product(FOM)
- Excellent Low Ciss
- Qualified according to JEDEC criteria

### Applications

- Switching application
- Li-battery protection
- DC-DC

### Benefits

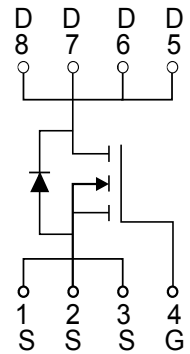
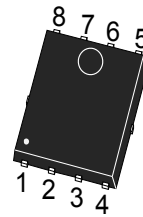
- High robustness and reliability
- Increases maximum current capability
- Low power loss, high power density
- Easy paralleling

### Product Summary

$V_{DS}$	60V
$R_{DS(on)@10V \text{ MAX}}$	5.0m $\Omega$
$I_D$	80A



### PDFN5060-8L



### Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	$V_{DS}$	60	V
Continuous drain current $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	$I_D$	80 55	A
Pulsed drain current ( $T_C = 25^\circ\text{C}$ , $t_p = 100\mu\text{s}$ )	$I_{D \text{ pulse}}$	360	A
Avalanche energy, single pulse ( $L=0.5\text{mH}$ , $V_{ds}=50\text{V}$ )	$E_{AS}$	121	mJ
Gate-Source voltage	$V_{GS}$	$\pm 20$	V
$P_D$ Power Dissipation $T_C = 25^\circ\text{C}$	78		W
Operating junction and storage temperature	$T_j, T_{stg}$	-55...+150	$^\circ\text{C}$
Soldering temperature, wave soldering only allowed at leads (1.6mm from case for 10s)	$T_{sold}$	260	$^\circ\text{C}$



### Thermal Resistance

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Thermal resistance, junction - case.	RthJC	-	-	1.6	°C/W	-

### Electrical Characteristic (at T<sub>j</sub> = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

### Static Characteristic

Drain-source breakdown voltage	BV <sub>DSS</sub>	60	-	-	V	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA
Gate threshold voltage	V <sub>GS(th)</sub>	1.2	-	2.5	V	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA
Zero gate voltage drain current	I <sub>DSS</sub>	-	0.02	1	μA	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V T <sub>j</sub> =25°C T <sub>j</sub> =150°C
Gate-source leakage current	I <sub>GSS</sub>	-	±10	±100	nA	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V
Drain-source on-state resistance	R <sub>DS(on)</sub>	-	4.05	5.0	mΩ	V <sub>GS</sub> =10V, I <sub>D</sub> =20A
		-	5.8	7.8	mΩ	V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A

### Dynamic Characteristic

Input Capacitance	C <sub>iss</sub>	-	2140	-	pF	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=300KHz
Output Capacitance	C <sub>oss</sub>	-	850	-		
Reverse Transfer Capacitance	C <sub>rss</sub>	-	60	-		
Gate Total Charge	Q <sub>G</sub>	-	30	-	nC	V <sub>DS</sub> =30V, I <sub>D</sub> =20A, V <sub>GS</sub> =10V
Gate-Source charge	Q <sub>gs</sub>	-	4.5	-		
Gate-Drain charge	Q <sub>gd</sub>	-	5	-		
Turn-on delay time	t <sub>d(on)</sub>	-	6.5	-	ns	V <sub>GS</sub> =10V, V <sub>DD</sub> =30V, R <sub>G_ext</sub> =5Ω, I <sub>D</sub> =20A
Rise time	t <sub>r</sub>	-	8	-		
Turn-off delay time	t <sub>d(off)</sub>	-	38	-		
Fall time	t <sub>f</sub>	-	16	-		



### Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	$V_{SD}$	-	0.77	1.2	V	$V_{GS}=0V, I_{SD}=30A$
Body Diode Continuous Forward Current	$I_S$	-	-	90	A	TC = 25°C
Body Diode Pulsed Current	$I_S$ pulse	-	-	360	A	TC = 25°C
Body Diode Reverse Recovery Time	$t_{rr}$	-	39	-	ns	$I_F=1A,$ $diF/dt=100A/\mu s$
Body Diode Reverse Recovery Charge	$Q_{rr}$	-	45	-	nC	



### Typical Performance Characteristics

Figure 1: Output Characteristics

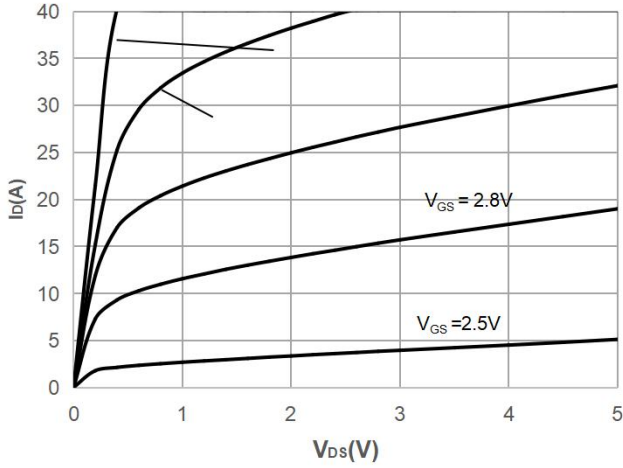


Figure 2: Typical Transfer Characteristics

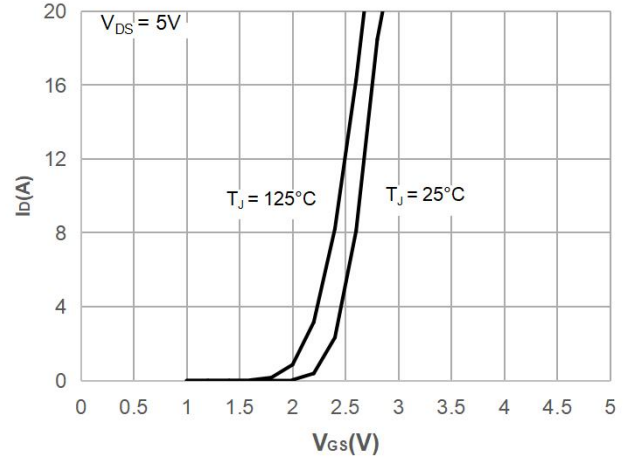


Figure 3: On-resistance vs. Drain Current

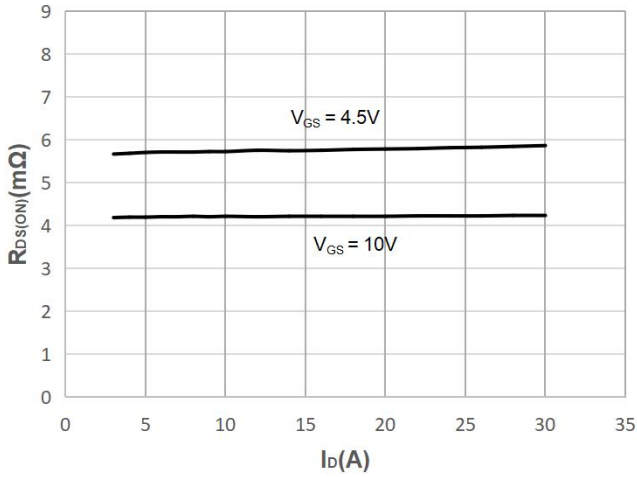


Figure 4: Body Diode Characteristics

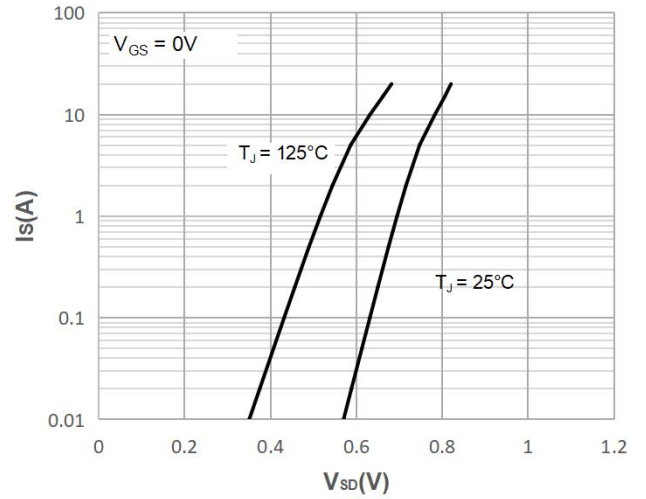


Figure 5: Gate Charge Characteristics

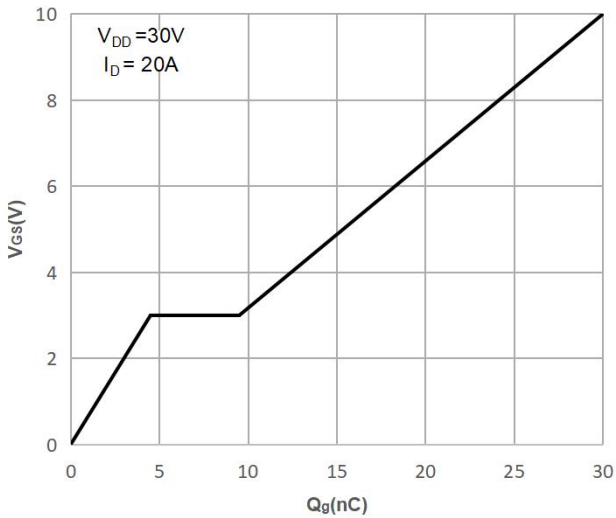


Figure 6: Capacitance Characteristics

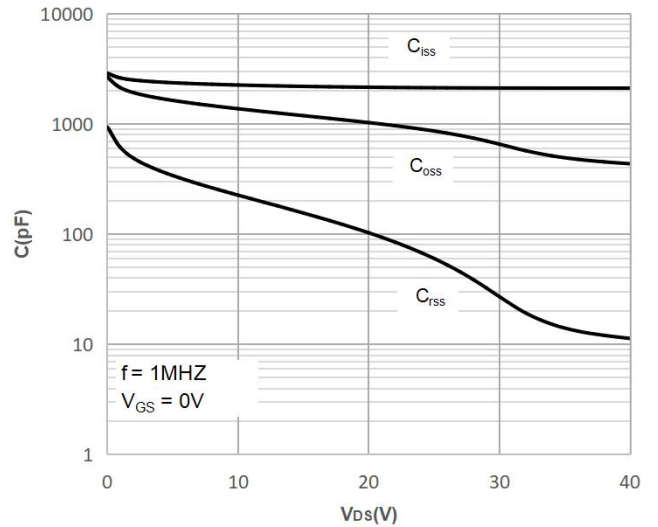


Figure 7: Normalized Breakdown voltage vs. Junction Temperature

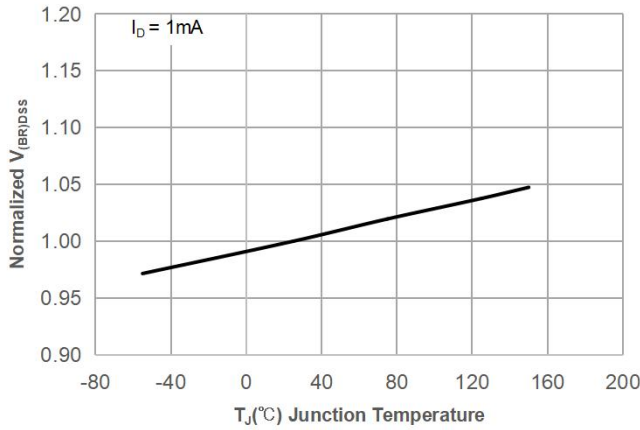


Figure 8: Normalized on Resistance vs. Junction Temperature

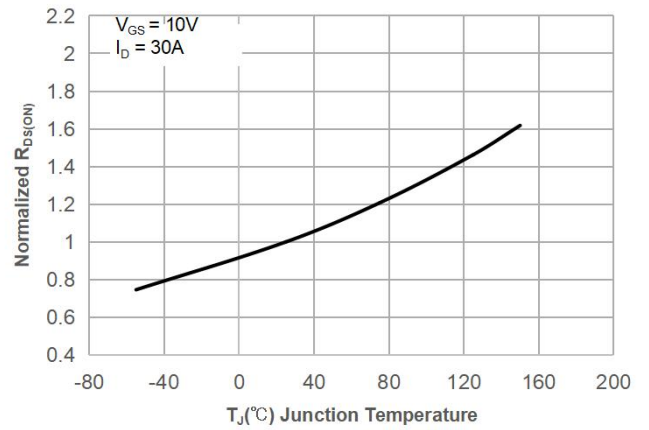


Figure 9: Maximum Safe Operating Area

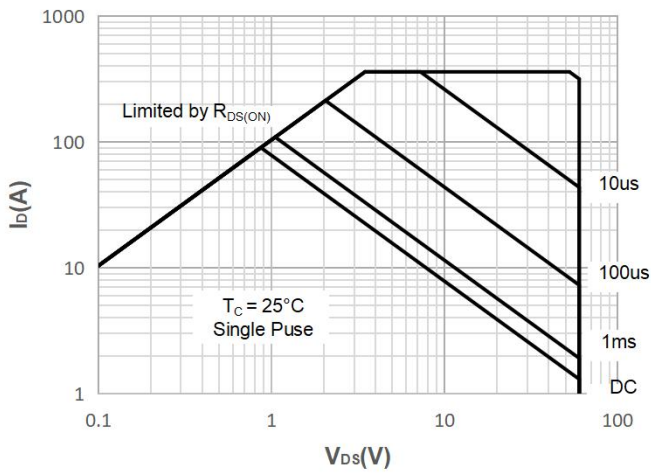


Figure 10: Maximum Continuous Driain Current vs. Case Temperature

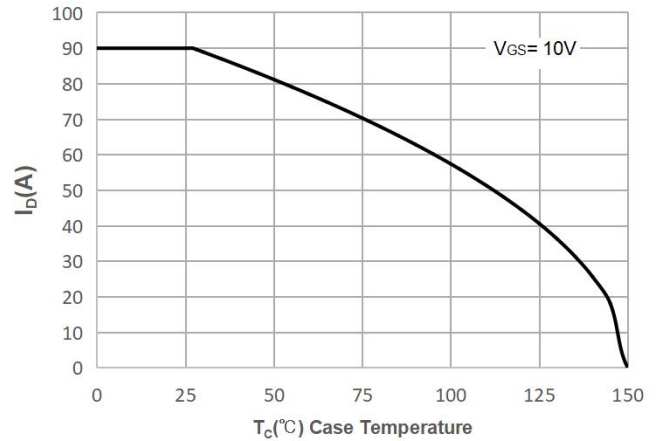


Figure 11: Normalized Maximum Transient Thermal Impedance

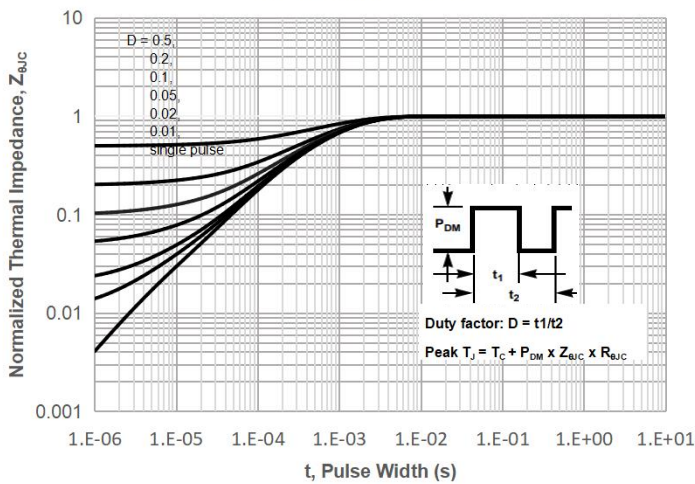
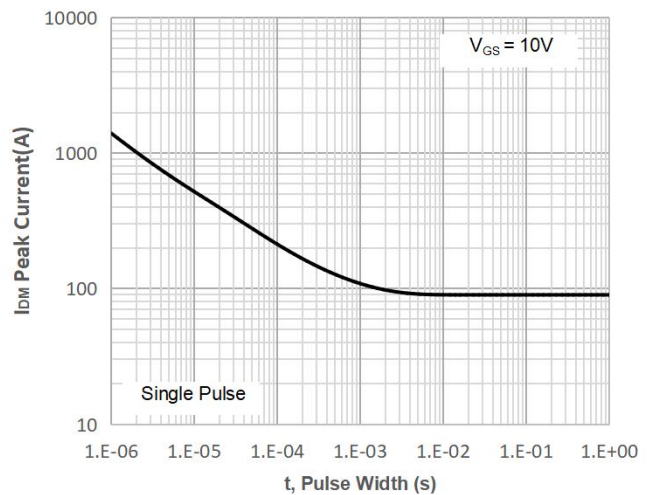
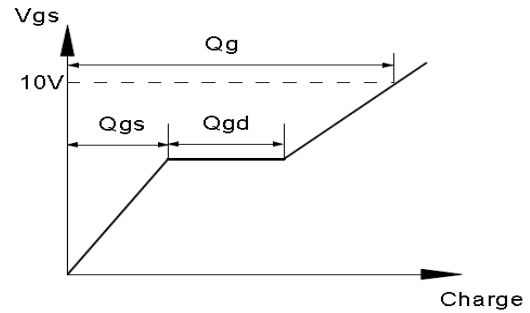
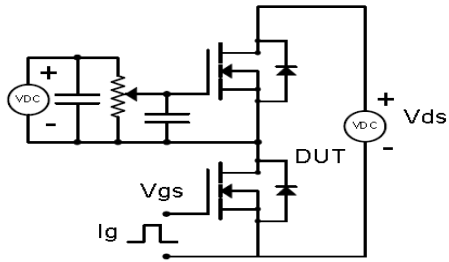


Figure 12: Peak Current Capacity

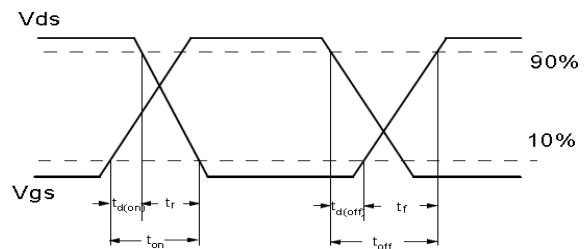
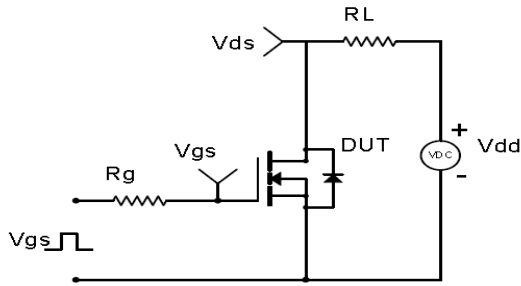


### Test Circuit & Waveform

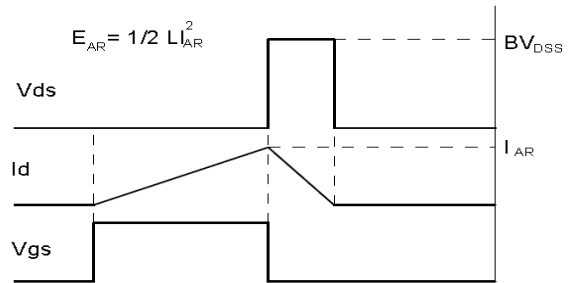
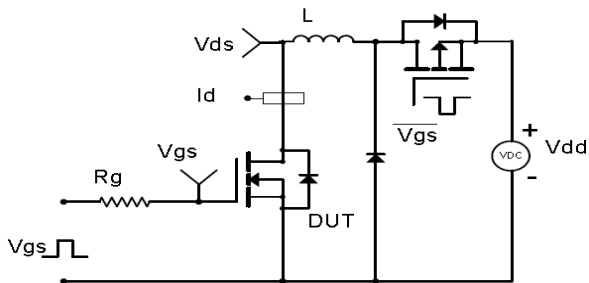
Gate Charge Test Circuit & Waveform



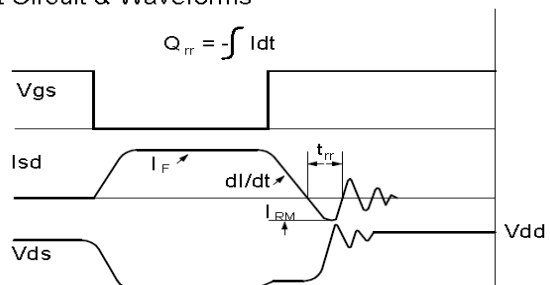
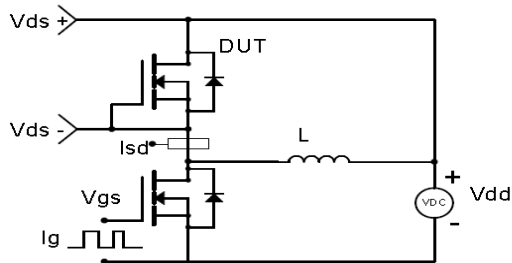
Resistive Switching Test Circuit & Waveforms



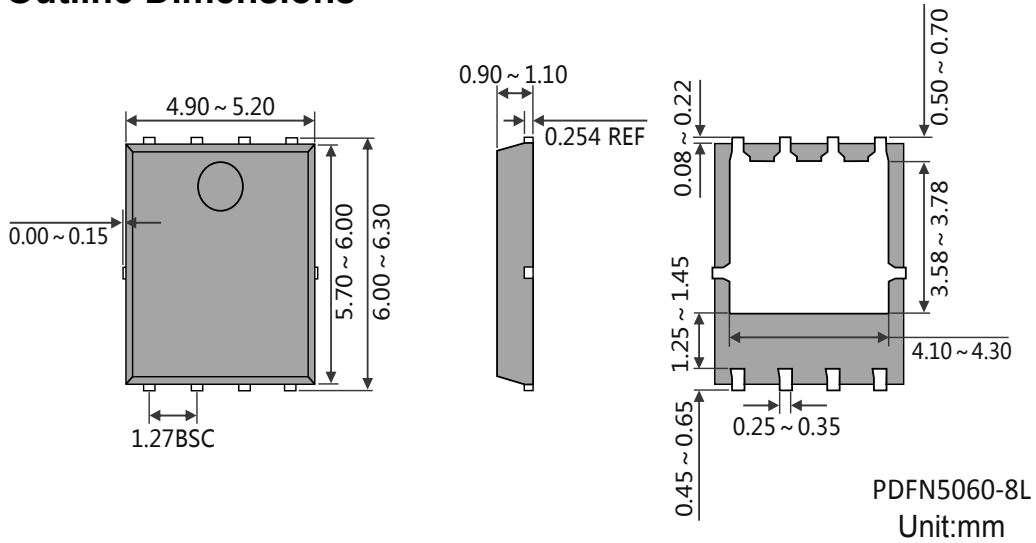
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



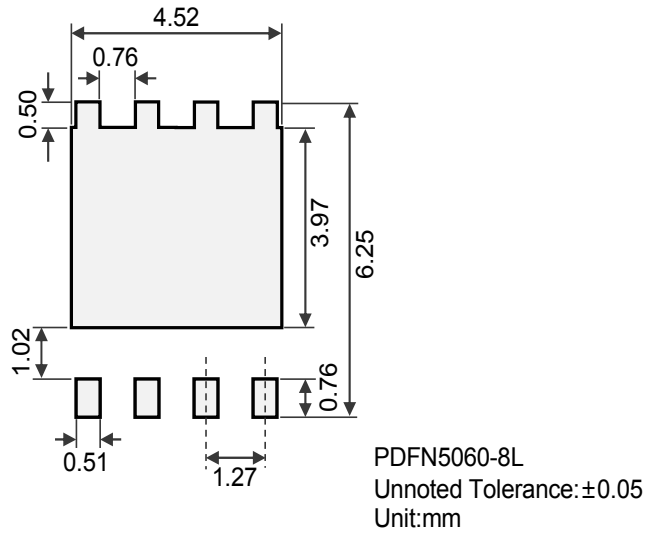
Diode Recovery Test Circuit & Waveforms



### Package Outline Dimensions



### Suggested Solder Pad Layout



### Marking Information

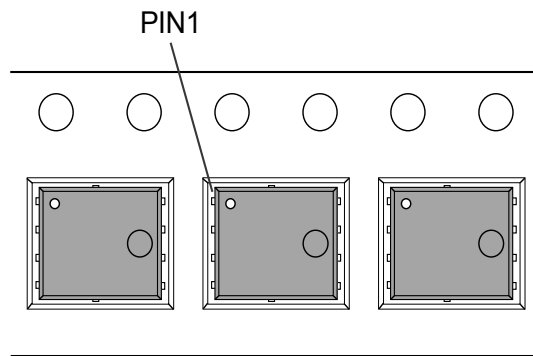


"MHCHXM" = Product Logo  
 "Marking Code" = The Following  
 "XXXX" = Date Code Marking

Marking Code	Part Number
S60N50LNA	HXMS60N50LNA



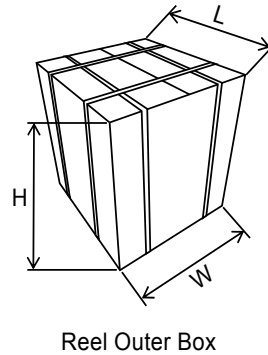
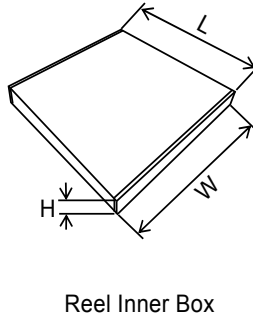
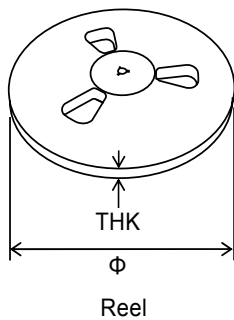
### The Orientation Of The Product In The Carrier Tape



### Packing Information

Packaging	Part Number	Quantity(pcs)	Size(mm)
Reel	Reel	5000	$\Phi 330 \times \text{THK}15$
	Inner Box	10000	L355×W335×H48
	Outer Box	80000	L415×W375×H360

Packaging:Reel



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2. The graphs shown in this datasheet are representing typical data only and do not show guaranteed values.
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